

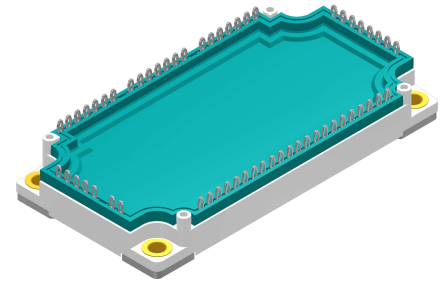
# High Voltage Standard Rectifier Module

<b>3~ Rectifier</b>
$V_{RRM} = 2200\text{ V}$
$I_{DAV} = 660\text{ A}$
$I_{FSM} = 5000\text{ A}$

3~ Rectifier Bridge + NTC

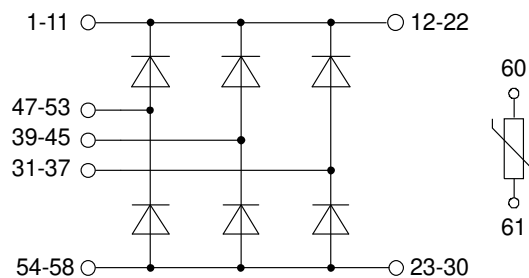
Part number

**MDNA660U2200PTEH**



Backside: isolated

 E72873



### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

### Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

### Package: E3-Pack

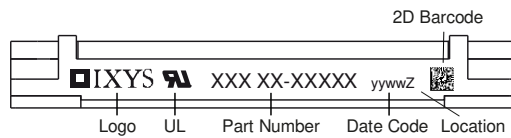
- Isolation Voltage: 4300 V~
- Industry standard outline
- RoHS compliant
- PressFit-Pins for PCB mounting
- Height: 17 mm
- Base plate: Copper internally DCB isolated
- Advanced power cycling
- Phase Change Material available

### Disclaimer Notice

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage			$T_{VJ} = 25^{\circ}C$		2300	V
$V_{RRM}$	max. repetitive reverse blocking voltage			$T_{VJ} = 25^{\circ}C$		2200	V
$I_R$	reverse current	$V_R = 2200\text{ V}$		$T_{VJ} = 25^{\circ}C$		400	$\mu A$
		$V_R = 2200\text{ V}$		$T_{VJ} = 150^{\circ}C$		6	mA
$V_F$	forward voltage drop	$I_F = 220\text{ A}$		$T_{VJ} = 25^{\circ}C$		1.28	V
		$I_F = 660\text{ A}$				1.95	V
		$I_F = 220\text{ A}$		$T_{VJ} = 125^{\circ}C$		1.19	V
		$I_F = 660\text{ A}$				1.95	V
$I_{DAV}$	bridge output current	$T_C = 85^{\circ}C$		$T_{VJ} = 150^{\circ}C$		660	A
		rectangular	$d = \frac{1}{3}$				
$V_{FO}$	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}C$		0.77	V
$r_F$	slope resistance					1.8	m $\Omega$
$R_{thJC}$	thermal resistance junction to case					0.15	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.075		K/W
$P_{tot}$	total power dissipation			$T_C = 25^{\circ}C$		830	W
$I_{FSM}$	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$		$T_{VJ} = 45^{\circ}C$		5.00	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$		$V_R = 0\text{ V}$		5.40	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$		$T_{VJ} = 150^{\circ}C$		4.25	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$		$V_R = 0\text{ V}$		4.59	kA
$I^2t$	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$		$T_{VJ} = 45^{\circ}C$		125.0	kA <sup>2</sup> s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$		$V_R = 0\text{ V}$		121.3	kA <sup>2</sup> s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$		$T_{VJ} = 150^{\circ}C$		90.3	kA <sup>2</sup> s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$		$V_R = 0\text{ V}$		87.6	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 700\text{ V}; f = 1\text{ MHz}$		$T_{VJ} = 25^{\circ}C$		158	pF

Package E3-Pack		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			30	A
$T_{VJ}$	virtual junction temperature		-40		175	°C
$T_{op}$	operation temperature		-40		150	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				270		g
$M_D$	mounting torque		3		6	Nm
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	12.0			mm
$V_{ISOL}$	isolation voltage	t = 1 second t = 1 minute	4300 3600			V
		50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA				V


**Part description**

M = Module  
 D = Diode  
 N = High Voltage Standard Rectifier  
 A = ( $\geq 2000V$ )  
 660 = Current Rating [A]  
 U = 3- Rectifier Bridge  
 2200 = Reverse Voltage [V]  
 PT = PressFit-Pin, Thermistor  
 EH = E3-Pack  
 - = Hyphen  
 PC = Phase Change Material

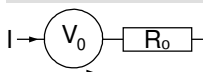
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDNA660U2200PTEH	MDNA660U2200PTEH	Blister	24	516663
Alternative	MDNA660U2200PTEH-PC	MDNA660U2200PTEH	Blister	24	514482

**Temperature Sensor NTC**

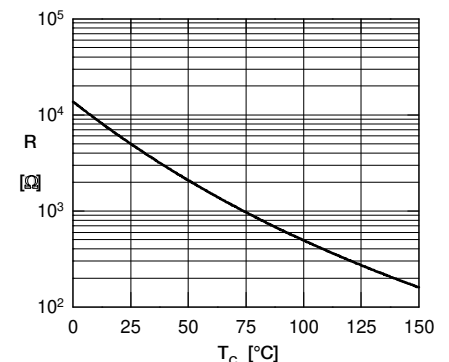
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$R_{25}$	resistance	$T_{VJ} = 25^\circ$	4.85	5	5.15	k $\Omega$
$B_{25/50}$	temperature coefficient			3375		K

**Equivalent Circuits for Simulation**

\* on die level

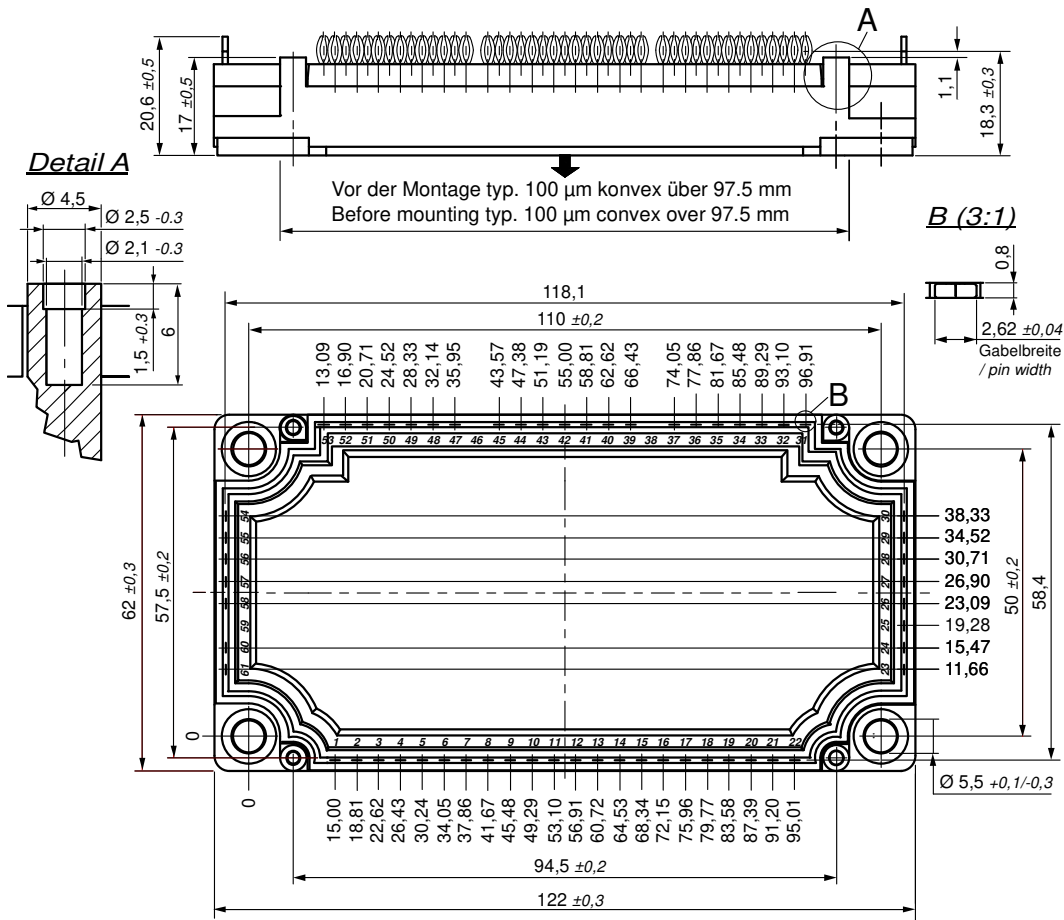
 $T_{VJ} = 150^\circ C$ 

**Rectifier**

$V_{0 \max}$	threshold voltage	0.77				V
$R_{0 \max}$	slope resistance *	0.57				m $\Omega$





**Outlines E3-Pack**

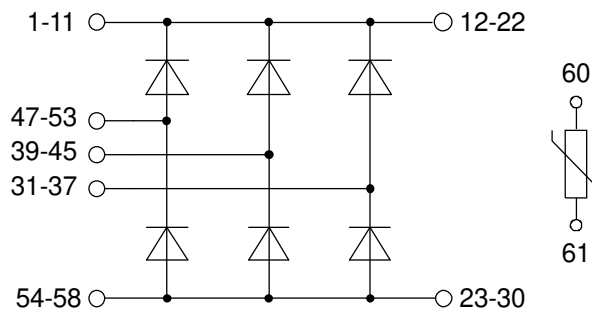


**Bemerkung / Note:**

- Nichttolerierete Maße nach / Measure without tolerances according DIN ISO 2768-T1-m
- PCB-Lochmuster / PCB hole pattern: **see pin position**
- Toleranz Pin-Position und PCB-Lochmuster / Tolerance of pin position and PCB hole pattern:  $\oplus 0.1$
- Bohrlochdurchmesser / Diameter of drill: **Ø 2.35 mm**
- Endlochdurchmesser / Diameter of plated holes: **Ø 2.14 - 2.29 mm** (Cu thickness in via typ. 50 µm)
- Beschichtung / Plating: **chem. Sn max. 15 µm**
- Einpresskraft / Insert Force: per terminal with a typ. insert speed of 7 mm/s: **typ. 90 N**
- Weitere Angaben / Further information: [www.ixys.com](http://www.ixys.com) **Application note IXAN0077**
- Montageanleitung / Mounting instruction: [www.ixys.com](http://www.ixys.com) **Application note IXAN0024**

**Detail A:** PCB-Montage / Mounting on PCB<sup>1</sup>

- Empfohlene, selbstschneidende Schraube / Recommended, self-tapping screw: **EJOT PT®** (Größe / size: **K25**)<sup>1</sup>
- Max. Schraubenlänge / Max. screw length: **PCB-Dicke / thickness + 6 mm** (max. Lochtiefe / hole depth)<sup>1</sup>
- Empfohlenes Drehmoment / Recommended mounting torque: **1.5 Nm**



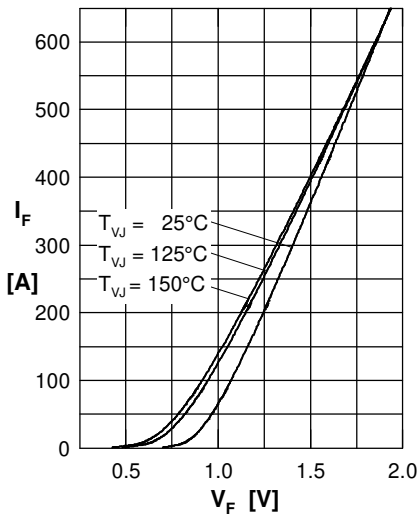
**Rectifier**


Fig. 1 Forward current versus voltage drop per diode

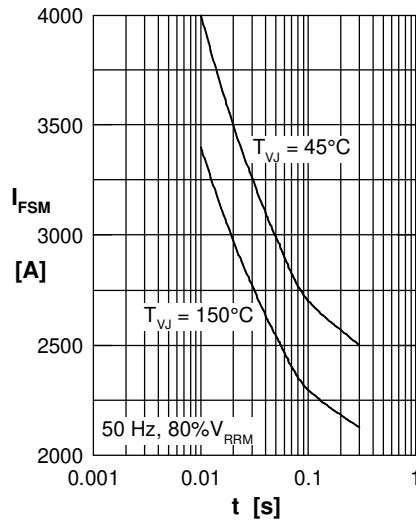


Fig. 2 Surge overload current vs. time per diode

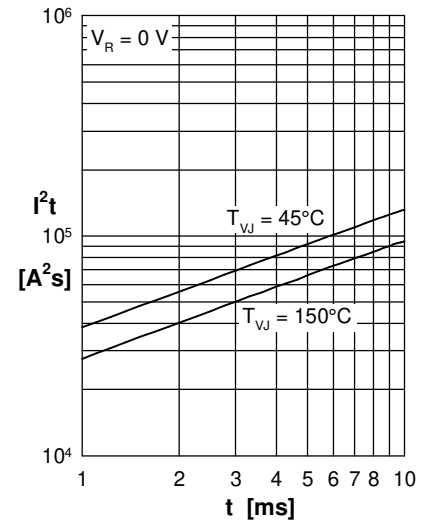
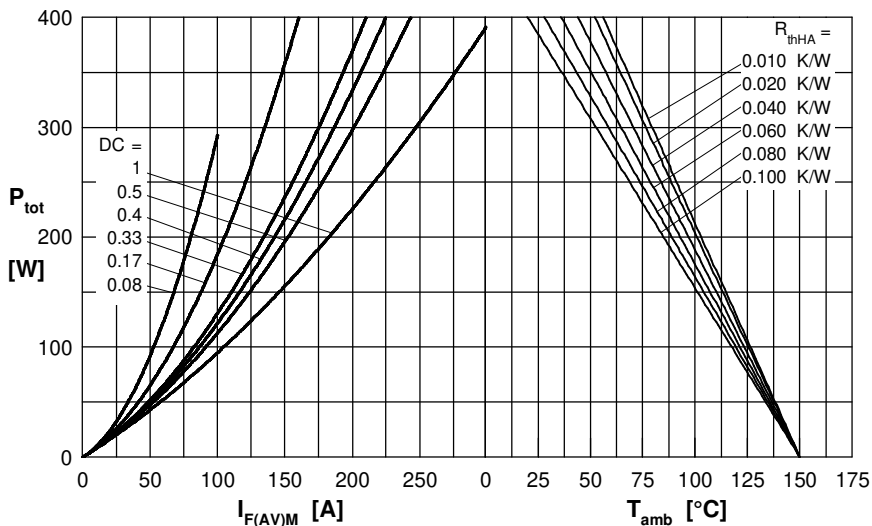

 Fig. 3  $I^2t$  versus time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

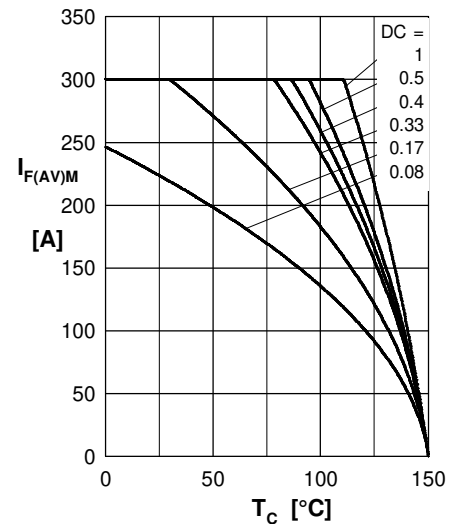


Fig. 5 Max. forward current vs. case temperature per diode

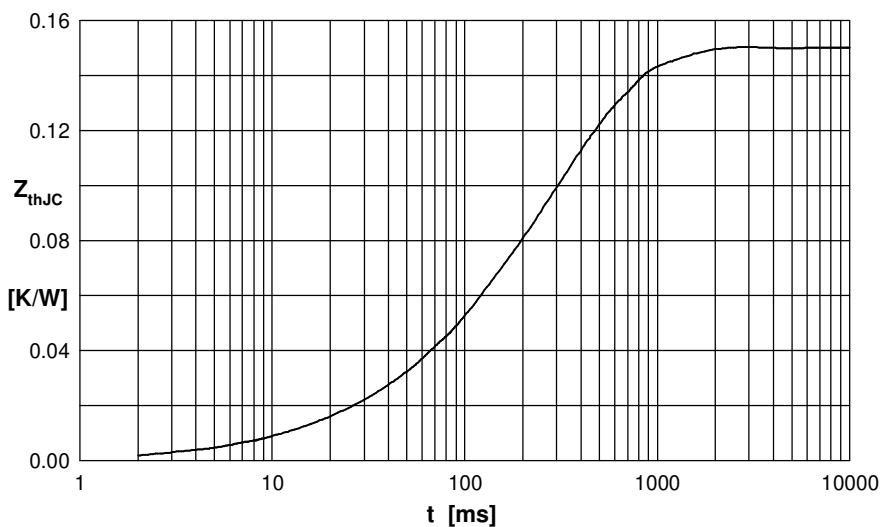


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.006	0.015
2	0.017	0.080
3	0.039	0.220
4	0.088	0.380